

# Jaikwang Shin

## List of Publications by Year in descending order

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18  
papers

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citations

759233

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h-index

940533

16  
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docs citations

18  
times ranked

1296  
citing authors

#	ARTICLE	IF	CITATIONS
1	p-GaN Gate HEMTs With Tungsten Gate Metal for High Threshold Voltage and Low Gate Current. IEEE Electron Device Letters, 2013, 34, 202-204.	3.9	213
2	A comparative study of structural changes in lithium nickel cobalt manganese oxide as a function of Ni content during delithiation process. Journal of Power Sources, 2016, 315, 111-119.	7.8	122
3	Deep-learning-based inverse design model for intelligent discovery of organic molecules. Npj Computational Materials, 2018, 4, .	8.7	91
4	Electrically driven mid-submicrometre pixelation of InGaN micro-light-emitting diode displays for augmented-reality glasses. Nature Photonics, 2021, 15, 449-455.	31.4	91
5	Interfacial adhesion behavior of polyimides on silica glass: A molecular dynamics study. Polymer, 2016, 98, 1-10.	3.8	59
6	Verification of Interface State Properties of a-InGaZnO Thin-Film Transistors With $\text{SiN}_x$ and $\text{SiO}_2$ Gate Dielectrics by Low-Frequency Noise Measurements. IEEE Electron Device Letters, 2011, 32, 1083-1085.	3.9	48
7	Asymmetric Doping in Silicon Nanostructures: The Impact of Surface Dangling Bonds. Nano Letters, 2010, 10, 1671-1676.	9.1	38
8	The impact of active layer thickness on low-frequency noise characteristics in InZnO thin-film transistors with high mobility. Applied Physics Letters, 2012, 100, .	3.3	38
9	Source-Connected p-GaN Gate HEMTs for Increased Threshold Voltage. IEEE Electron Device Letters, 2013, 34, 605-607.	3.9	35
10	Influence of Hf contents on interface state properties in <i>a</i> -HfInZnO thin-film transistors with SiNx/SiOx gate dielectrics. Applied Physics Letters, 2011, 99, .	3.3	32
11	Overview of the Oxygen Behavior in the Degradation of $\text{Li}_2\text{MnO}_3$ Cathode Material. Journal of Physical Chemistry C, 2017, 121, 21118-21127.	3.1	30
12	Computational approaches for investigating interfacial adhesion phenomena of polyimide on silica glass. Scientific Reports, 2017, 7, 10475.	3.3	27
13	Characterization of traps and trap-related effects in recessed-gate normally-off AlGaIn/GaN-based MOSHEMT. , 2012, , .		18
14	Impacts of fluorine on GaN high electron mobility transistors: Theoretical study. Physica Status Solidi - Rapid Research Letters, 2010, 4, 332-334.	2.4	10
15	The prediction of hole mobility in organic semiconductors and its calibration based on the grain-boundary effect. Physical Chemistry Chemical Physics, 2016, 18, 21371-21380.	2.8	9
16	Analysis of DC/transient current and RTN behaviors related to traps in p-GaN gate HEMT. , 2013, , .		7
17	Surface Ferromagnetic p-Type ZnO Nanowires through Charge Transfer Doping. ACS Applied Materials & Interfaces, 2012, 4, 1365-1370.	8.0	5
18	Understanding the grain-growth mechanism of high-performance organic semiconducting diphenyl-dibenzothiopheno[6,5-b:6'5'-f]thieno[3,2-b]thiophene molecules. Applied Physics Letters, 2017, 111, 233301.	3.3	2